

Abstract

Since a plurality of light-receiving elements have heretofore led an electrode from a semiconductor substrate through an impurity-diffused and -buried region, series resistance has been relatively high, so that it has been difficult to improve the frequency characteristics of the light-receiving element. The present invention reduces parasitic capacitance by isolating the light-receiving elements from one another with insulator or dielectric isolation regions 6 and further reduces series resistance by making a direct contact with a P-type semiconductor substrate 2 functioning as an anode region through the medium of a conductor-buried region 11 formed by burying a low-resistance conductor in an opening formed in the isolation region 6, so that the frequency characteristics of the light-receiving element can be improved.